

## Amendments to the Claims

This listing of claims will replace all prior versions, and listings of claims in the application.

### **Listing of Claims:**

1-11. (cancelled).

12. (currently amended): A method for fabricating a semiconductor device, comprising:

forming a contact hole in an organic insulating layer using a patterned resist layer formed over the organic insulating layer as a mask; and

ashing the patterned resist layer by a plasma treatment in the presence of a mixed gas of O<sub>2</sub>+N<sub>2</sub>H<sub>2</sub> consisting of nitrogen, oxygen and hydrogen, and forming a protective film on a surface of the contact hole during said ashing, wherein a ratio of O<sub>2</sub> to N<sub>2</sub>H<sub>2</sub> in the mixed gas is 90:10, and wherein the protective film is formed by reacting the organic insulating layer with the nitrogen.

13. (currently amended): A method as claimed in claim 12, wherein the mixed gas consists of O<sub>2</sub>+N<sub>2</sub>H<sub>2</sub> plasma treatment is carried out at a pressure of 0.45Pa and at a temperature of 100°C.

14. (currently amended): A method for fabricating a semiconductor device, comprising:

forming an organic spin-on-glass (SOG) film over an interconnect layer;

forming a contact hole in the organic SOG insulating layer so as to expose the interconnect layer using a patterned resist layer formed over the organic SOG insulating layer as a mask; and

ashing the patterned resist layer by a plasma treatment in the presence of a mixed gas of O<sub>2</sub>+N<sub>2</sub>H<sub>2</sub> consisting of nitrogen, oxygen and hydrogen, and forming a protective film on a surface of the contact hole during said ashing, wherein a ratio of O<sub>2</sub> to N<sub>2</sub>H<sub>2</sub> in the mixed gas is 90:10, and wherein the protective film is formed by reacting the organic SOG insulating layer with the nitrogen.

15. (original): The method as claimed in claim 14, wherein a material of the organic SOG layer is obtained by adding an alkyl group to a silicon oxide.

16. (currently amended): A method as claimed in claim 15, wherein the mixed gas consists of O<sub>2</sub>+N<sub>2</sub>H<sub>2</sub> plasma treatment is carried out at a pressure of 0.45Pa and at a temperature of 100°C.

17. (currently amended): A method as claimed in claim 14, wherein the mixed gas consists of O<sub>2</sub>+N<sub>2</sub>H<sub>2</sub> plasma treatment is carried out at a pressure of 0.45Pa and at a temperature of 100°C.